MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride

Tech ID: 21917 / UC Case 2005-566-0

BRIEF DESCRIPTION

Methods for successfully growing planar non-polar m-plane gallium nitride (GaN) with metalorganic chemical vapor deposition (MOCVD).

BACKGROUND

It is relatively easy to grow c-plane GaN due to its large growth window (pressure, temperature and precursor flows) and its stability. However, as a result of c-plane growth, each material layer suffers from separation of electrons and holes to opposite faces of the layers. Furthermore, strain at the interfaces between adjacent layers gives rise to piezoelectric polarization, causing further charge separation. Such polarization effects decrease the likelihood of electrons and holes recombining, causing the device to perform poorly.

DESCRIPTION

Researchers at the University of California, Santa Barbara have developed methods for successfully growing planar non-polar m-plane gallium nitride (GaN) with metalorganic chemical vapor deposition (MOCVD). These methods take advantage of non-polar nature of m-plane GaN to eliminate polarization fields, and gives rise to flexibility in growth variables, such as temperature, pressure and precursor flows, utilizing the advantage of m-GaN stability during growth.

ADVANTAGES

- Eliminates polarization fields
- More flexibility in growth variables

APPLICATIONS

Growth of non-polar GaN films

GaN-based devices

This technology is available for a non-exclusive license. See below for a selection of the patents and patent applications related to this invention. Please inquire for full patent portfolio status.

PATENT STATUS

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<th>Type</th>
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<td>United States Of America</td>
<td>Issued Patent</td>
<td>8,795,440</td>
<td>08/05/2014</td>
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<td>8,097,481</td>
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RELATED CASES

2005-566-0

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- Enhanced Optical Polarization of Nitride LEDs by Increased Indium Incorporation
- Etching Technique for the Fabrication of Thin (Al, In, Ga)N Layers
Lateral Growth Method for Defect Reduction of Semipolar Nitride Films
Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
III-Nitride-Based Devices Grown With Relaxed Active Region
Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs (UC Case 2010-183)
Defect Reduction in GaN films using in-situ SiNx Nanomask
Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
Highly Efficient Blue-Violet III-Nitride Semipolar Laser Diodes
Hybrid Growth Method for Improved III-Nitride Tunnel Junction Devices
Low Temperature Deposition of Magnesium Doped Nitride Films
Transparent Mirrorless (TML) LEDs
Improved GaN Substrates Prepared with Ammonothermal Growth
Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
Size-Independent Forward Voltage Micro-LED with an Epitaxial Junction
Method for Enhancing Growth of Semipolar Nitride Devices
III-Nitride Tunnel Junction with Modified Interface
Growth of Polyhedron-Shaped Gallium Nitride Bulk Crystals
Nonpolar III-Nitride LEDs With Long Wavelength Emission
Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
Increased Light Extraction with Multistep Deposition of ZnO on GaN
Method for Manufacturing Improved III-Nitride LEDs and Laser Diodes: Monolithic Integration of Optically Pumped and Electrically Injected III-Nitride LEDs
Selective-Area Mesoporous Semiconductors And Devices For Optoelectronic And Photonic Applications
High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
Method for Growing High-Quality Group III-Nitride Crystals
Controlled Photoelectrochemical (PEC) Etching by Modification of Local Electrochemical Potential of Semiconductor Structure
Oxyfluoride Phosphors for Use in White Light LEDs
Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
(In,Ga,AI)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
Thermally Stable, Laser-Driven White Lighting Device
Reduced Dislocation Density of Non-Polar GaN Grown by Hydride Vapor Phase Epitaxy
Highly Compact, High-Index Dielectric Nanostructures for Deep-Ultraviolet Devices
Reduction in Leakage Current and Increase in Efficiency of III-Nitride MicroLEDs
Methods for Fabricating III-Nitride Tunnel Junction Devices
Low-Droop LED Structure on GaN Semi-polar Substrates
Contact Architectures for Tunnel Junction Devices
Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
Photoelectrochemical Etching Of P-Type Semiconductor Heterostructures
Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
III-Nitride-Based Devices Grown On Thin Template On Thermally Decomposed Material
Growth of Semipolar III-V Nitride Films with Lower Defect Density
III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
Improved Manufacturing of Solid State Lasers via Patterning of Photonic Crystals
High Efficiency III-Nitride Devices with Smooth Relaxed InGaN Buffer and Strain Compliant Template
Tunable White Light Based on Polarization-Sensitive LEDs
Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
Growth of High-Performance M-plane GaN Optical Devices
Packaging Technique for the Fabrication of Polarized Light Emitting Diodes
Improved Anisotropic Strain Control in Semipolar Nitride Devices
High Light Extraction Efficiency III-Nitride LED
III-V Nitride Device Structures on Patterned Substrates
Activation of P-Type Layers of Tunnel Junctions in Micro-LEDs
Method for Increasing GaN Substrate Area in Nitride Devices
Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
Growth of Planar, Non-Polar, A-Plane GaN by Hydride Vapor Phase Epitaxy
GaN-Based Thermoelectric Device for Micro-Power Generation
Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patterning
LED Device Structures with Minimized Light Re-Absorption
Growth of Planar Semi-Polar Gallium Nitride

Nonpolar (Al, B, In, Ga)N Quantum Well Design

UV Optoelectronic Devices Based on Nonpolar and Semi-polar AlInN and AlInGaN Alloys

Defect Reduction of Non-Polar and Semi-Polar III-Nitrides

III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture

Enhancing Growth of Semipolar (Al,In,Ga,B)N Films via MOCVD